

Amendments to the Claims:

Cancel Claims 1-18 without prejudice or disclaimer of the subject matter contained therein.

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-18. (Canceled)

19. (New) A method of fabricating a fluid ejection device, comprising:
fabricating a thinfilm structure on a device substrate;

forming a peripheral break trench structure in a first surface of the substrate circumscribing a region in which a feed slot is to be formed through the substrate;

subsequently abrasively machining the substrate from a second surface of the substrate to the break trench structure to form the feed slot.

20. (New) The method of Claim 19 further comprising;

applying a barrier layer to the thinfilm structure after forming the break trench structure and before abrasively machining the substrate.

21. (New) The method of Claim 19 wherein said fabricating the thinfilm structure includes fabricating the thinfilm structure on said first surface of the substrate.

22. (New) The method of Claim 19 wherein said forming a break trench structure includes anisotropically etching the trench during a wet etch process.

23. (New) The method of Claim 19, further including:
forming a guide break trench in said first surface within the peripheral break trench structure.

24. (New) The method of Claim 23, wherein said guide break trench structure is formed to a depth deeper than a depth of said peripheral break trench structure.

25. (New) The method of Claim 24, wherein the guide break trench structure is formed with a trench width greater than a width of said peripheral break trench structure.

26. (New) The method of Claim 19, wherein the substrate is a silicon substrate, and wherein said forming a break trench structure includes:
etching the silicon substrate with a TMAH (Tetra Methyl Ammonium Hydroxide) wet etch process.

27. (New) A fluid ejection device produced by the method of Claim 19.

28. (New) A method of fabricating a fluid ejection device, comprising:
fabricating a thinfilm structure on a device substrate;
forming a break trench structure in a first surface of the substrate, said structure comprising a plurality of small break trenches arranged along a slot axis;
subsequently abrasively machining the substrate from a second surface of the substrate to the plurality of break trenches to form a plurality of small feed slots through the substrate.

29. (New) The method of Claim 28, further comprising:
defining a plurality of small substrate islands in areas separating the small slots.

30. (New) The method of Claim 29, wherein said defining a plurality of small substrate islands comprises:

- forming a mask structure defining the islands;
- etching the first surface through the mask structure to define the plurality of small substrate islands.

31. (New) The method of Claim 28, wherein said substrate is a silicon substrate, and wherein said forming a break trench structure includes:

- etching the silicon substrate with a TMAH (Tetra Methyl Ammonium Hydroxide) wet etch process.

32. (New) A fluid ejection device produced by the method of Claim 28.

33. (New) A method of fabricating a fluid ejection device, comprising:
fabricating a thinfilm structure on a substrate wafer for a plurality of fluid ejection devices to be formed on the wafer;

- for each printhead to be formed, forming a peripheral break trench structure in a first surface of the substrate circumscribing a region in which a feed slot is to be formed through the substrate for each fluid ejection device to be formed on the wafer;

- applying a barrier layer to the thinfilm structure;

- subsequently abrasively machining the wafer from a second surface of the substrate to the peripheral break trench structure to form the feed slot for each fluid ejection device to be formed on the wafer;

- attaching an orifice plate structure for each fluid ejection device to be formed on the wafer;

- sawing the wafer to separate individual fluid ejection devices; and

- attaching the fluid ejection devices to device circuitry.